

EVVOSEMI[®]

THINK CHANGE DO



ESD



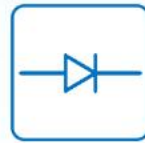
TVS



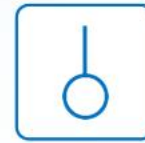
MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	NDC7002N
▶ Overseas	Part Number	NDC7002N
▶ Equivalent	Part Number	NDC7002N

EV is the abbreviation of name EVVO

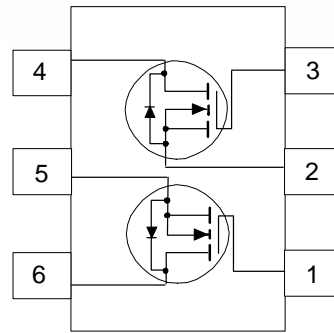
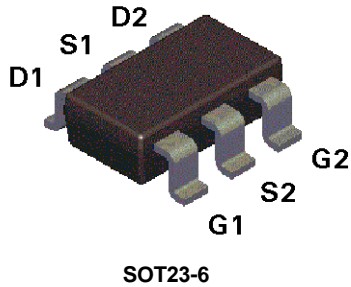
SOT23-6 Dual N-Channel Enhancement Mode Field Effect Transistor

General Description

These dual N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been designed to minimize on-state resistance, provide rugged and reliable performance and fast switching. These devices is particularly suited for low voltage applications requiring a low current high side switch.

Features

- 0.51A, 50V, $R_{DS(ON)} = 2\Omega @ V_{GS}=10V$
- High density cell design for low $R_{DS(ON)}$.
- Proprietary SOT23-6 package design using copper lead frame for superior thermal and electrical capabilities.
- High saturation current.



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter		NDC7002N	Units
V_{DSS}	Drain-Source Voltage		50	V
V_{GSS}	Gate-Source Voltage - Continuous		20	V
I_D	Drain Current - Continuous	(Note 1a)	0.51	A
	- Pulsed		1.5	
P_D	Maximum Power Dissipation	(Note 1a)	0.96	W
		(Note 1b)	0.9	
		(Note 1c)	0.7	
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to 150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	130	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	60	$^\circ\text{C/W}$

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
OFF CHARACTERISTICS							
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	50			V	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$			1	μA	
			$T_J = 125^\circ\text{C}$		500		
I_{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA	
I_{GSSR}	Gate - Body Leakage, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA	
ON CHARACTERISTICS (Note 2)							
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1	1.9	2.5	V	
			$T_J = 125^\circ\text{C}$	0.8	1.5	2.2	
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 0.51\text{ A}$		1	2	Ω	
			$T_J = 125^\circ\text{C}$		1.7	3.5	
			$V_{GS} = 4.5\text{ V}, I_D = 0.35\text{ A}$		1.6	4	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 10\text{ V}$	1.5			A	
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 0.51\text{ A}$		400		mS	
DYNAMIC CHARACTERISTICS							
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		20		pF	
C_{oss}	Output Capacitance			13		pF	
C_{rss}	Reverse Transfer Capacitance			5		pF	
SWITCHING CHARACTERISTICS (Note 2)							
$t_{D(on)}$	Turn - On Delay Time	$V_{DD} = 25\text{ V}, I_D = 0.25\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 25\ \Omega$		6	20	nS	
t_r	Turn - On Rise Time			6	20		
$t_{D(off)}$	Turn - Off Delay Time			11	20		
t_f	Turn - Off Fall Time			5	20		
Q_g	Total Gate Charge	$V_{DS} = 25\text{ V},$ $I_D = 0.51\text{ A}, V_{GS} = 10\text{ V}$		1		nC	
Q_{gs}	Gate-Source Charge			0.19		nC	
Q_{gd}	Gate-Drain Charge			0.33		nC	

SOT23-6 Dual N-Channel Enhancement Mode Field Effect Transistor

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
DRAIN-SOURCE DIODE CHARACTERISTICS						
I _S	Maximum Continuous Source Current				0.51	A
I _{SM}	Maximum Pulse Source Current (Note 2)				1.5	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 0.51 A (Note 2)		0.8	1.2	V

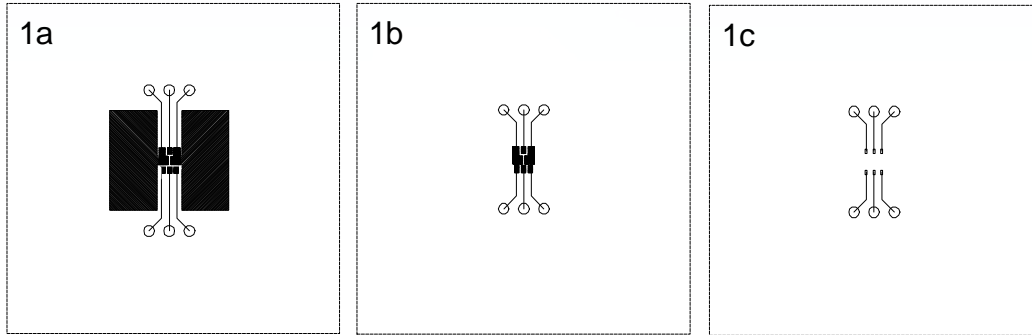
Notes:

1. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design while R_{θJA} is determined by the user's board design.

$$P_D(t) = \frac{I_D I_A}{R_{\theta J A}} = \frac{I_D I_A}{R_{\theta J C} + R_{\theta C A}(t)} = I_D^2(t) \times R_{DS(on)} \theta_{J A}$$

Typical R_{θJA} for single device operation using the board layouts shown below on 4.5"x5" FR-4 PCB in a still air environment:

- a. 130°C/W when mounted on a 0.125 in² pad of 2oz copper.
- b. 140°C/W when mounted on a 0.005 in² pad of 2oz copper.
- c. 180°C/W when mounted on a 0.0015 in² pad of 2oz copper.



Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%.

SOT23-6 Dual N-Channel Enhancement Mode Field Effect Transistor

Typical Electrical Characteristics

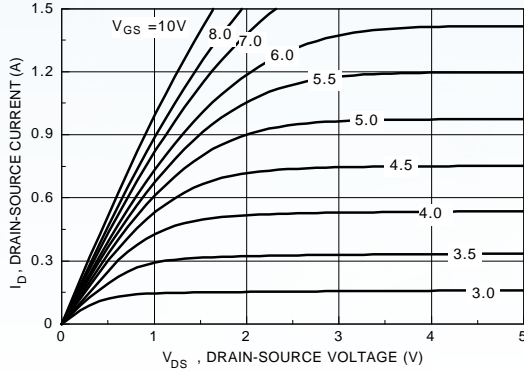


Figure 1. On-Region Characteristics.

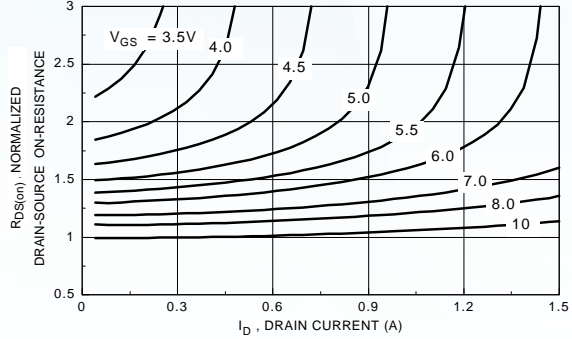


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.

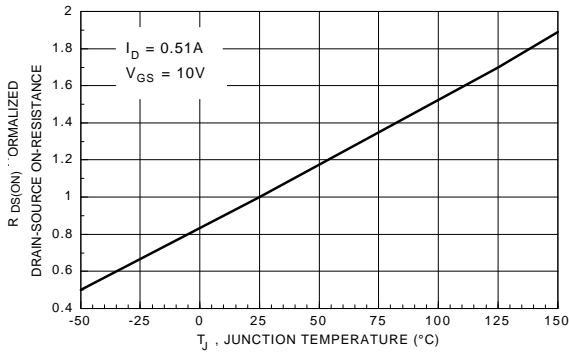


Figure 3. On-Resistance Variation with Temperature.

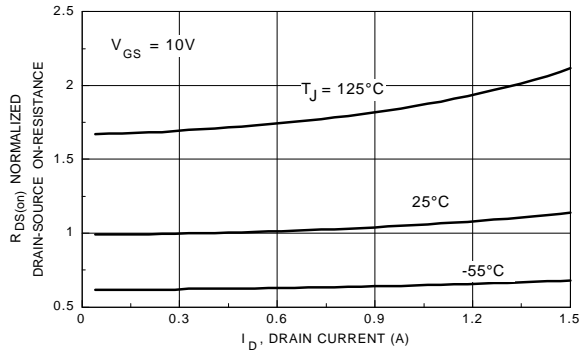


Figure 4. On-Resistance Variation with Drain Current and Temperature.

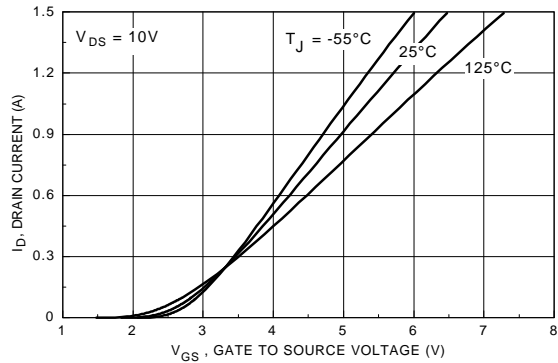


Figure 5. Transfer Characteristics.

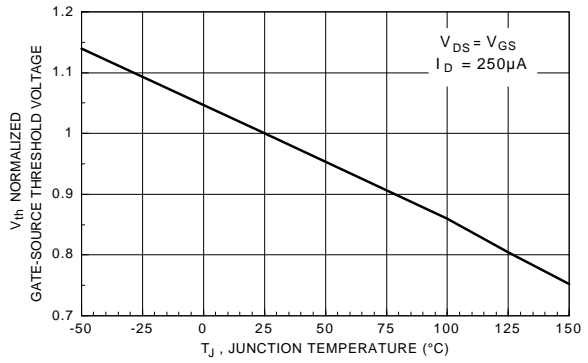


Figure 6. Gate Threshold Variation with Temperature.

SOT23-6 Dual N-Channel Enhancement Mode Field Effect Transistor

Typical Electrical Characteristics (continued)

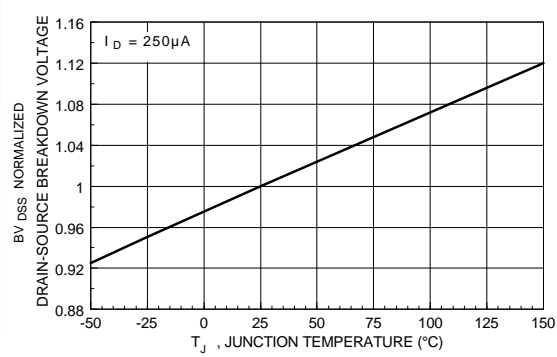


Figure 7. Breakdown Voltage Variation with Temperature.

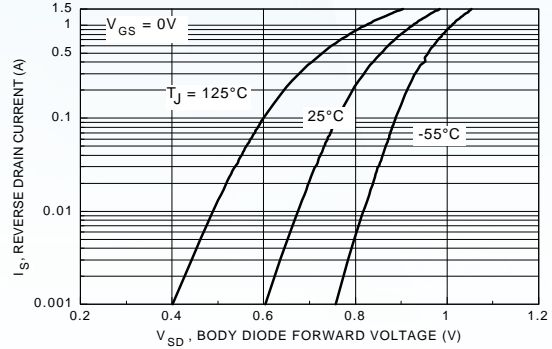


Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.

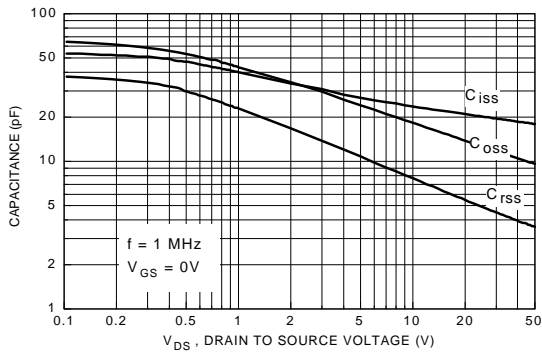


Figure 9. Capacitance Characteristics.

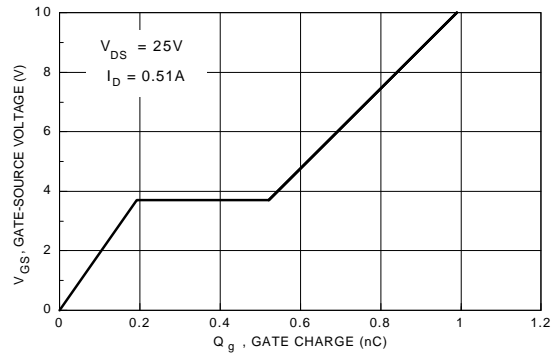


Figure 10. Gate Charge Characteristics.

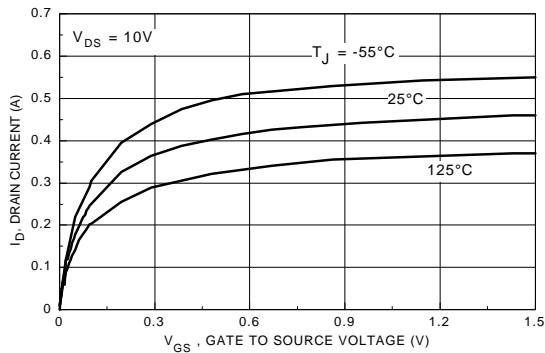


Figure 11. Transconductance Variation with Drain Current and Temperature.

SOT23-6 Dual N-Channel Enhancement Mode Field Effect Transistor

Typical Thermal Characteristics

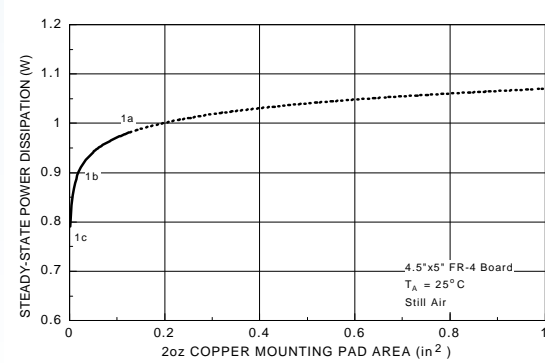


Figure 12. SOT23-6 Dual Package Maximum Steady-State Power Dissipation versus Copper Mounting Pad Area.

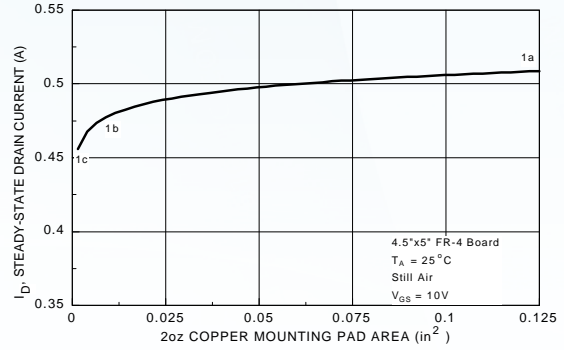


Figure 13. Maximum Steady-State Drain Current versus Copper Mounting Pad Area.

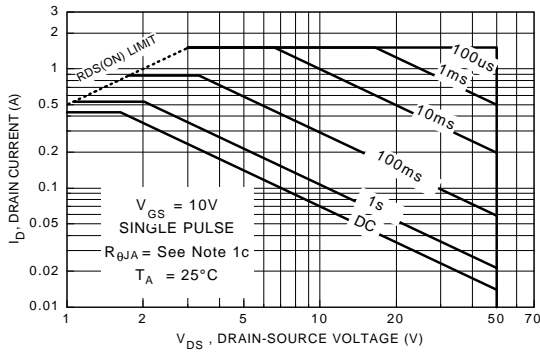
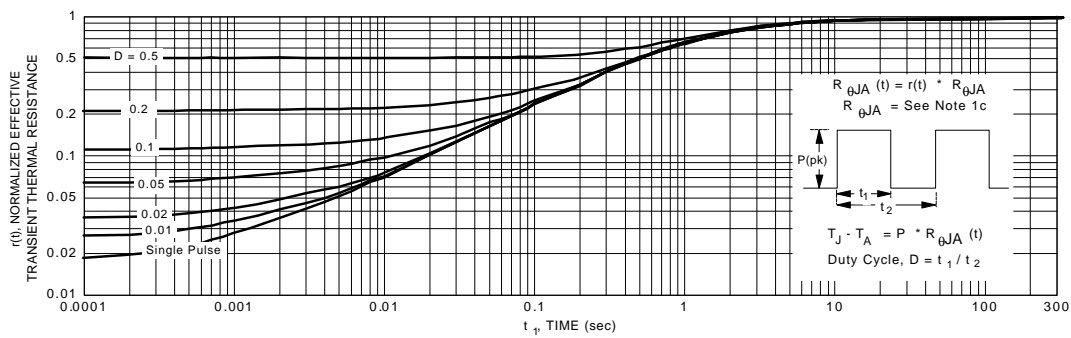
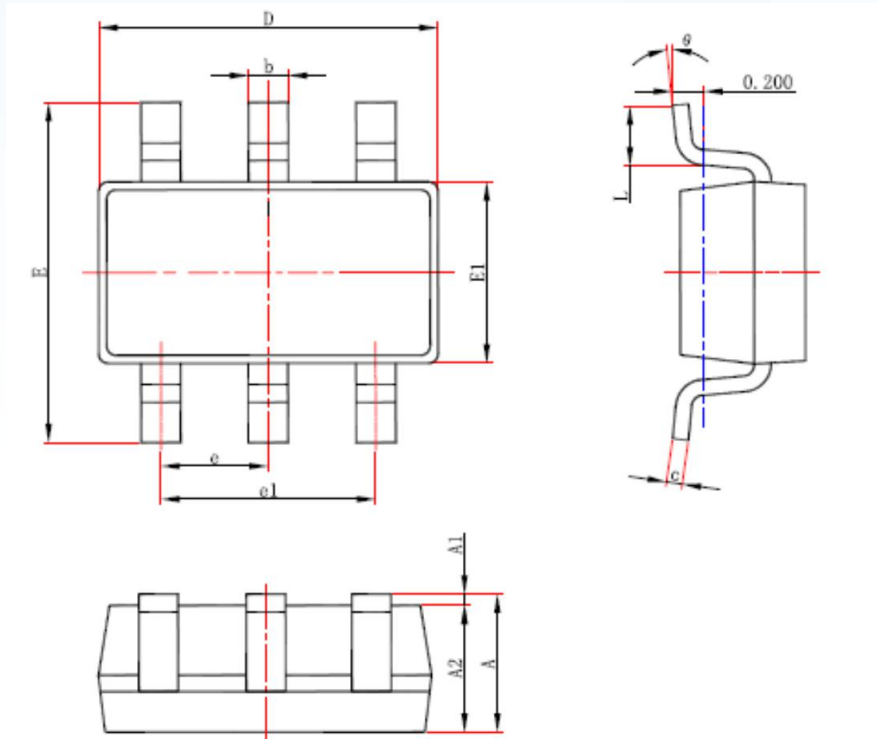


Figure 14. Maximum Safe Operating Area.



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SOT23-6



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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